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PATENT NUMBER

U.S. UTILITY Patent Application

SCANNED AS DATE

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Gishi Chung	:	
Fabrication process of a semiconductor device inclu- process of a metal film	ding a CVD	

	ISSUING C	LASSIFICATION
ORIGINAL		CROSS REFERENCE(S)
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TERMINAL	DRAWINGS	CLAIMS ALLOWED
DISCLAIMER	Sheets Drwg: Figs Drwg: Print Fig.	Total Claims 3 Print Claim for O.G.
The term of this patent subsequent to (date)	(Outo)	NOTICE OF ALLOWANCE MAILED
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